

PFU7N60EG / PFD7N60EG

600V N-Channel MOSFET

FEATURES

- ❑ Originative New Design
- ❑ 100% EAS Test
- ❑ Rugged Gate Oxide Technology
- ❑ Extremely Low Intrinsic Capacitances
- ❑ Remarkable Switching Characteristics
- ❑ Unequalled Gate Charge : 17 nC (Typ.)
- ❑ Extended Safe Operating Area
- ❑ Lower $R_{DS(ON)}$: 1.20 Ω (Typ.) @ $V_{GS}=10V$
- ❑ Halogen Free

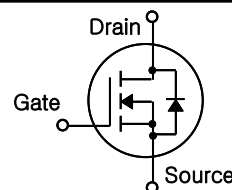
APPLICATION

- ❑ High current, High speed switching
- ❑ Suitable for power supplies, adaptors and PFC
- ❑ SMPS (Switched Mode Power Supplies)

$$BV_{DSS} = 600 V$$

$$R_{DS(on)} = 1.20 \Omega$$

$$I_D = 5.8 A$$

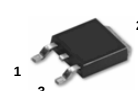


I-PAK(TO-251)



1.Gate 2. Drain 3. Source

D-PAK(TO-252)



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

$T_C=25^\circ C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current – Continuous ($T_C = 25^\circ C$)	5.8	A
	Drain Current – Continuous ($T_C = 100^\circ C$)	3.7	A
I_{DM}	Drain Current – Pulsed (Note 1)	23.2	A
V_{GS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	98	mJ
I_{AR}	Avalanche Current (Note 1)	5.6	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	11.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$)	114	W
	- Derate above $25^\circ C$	0.91	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

* Drain current limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.10	$^\circ C/W$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	--	--	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	

Electrical Characteristics $T_C=25\text{ }^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	--	1.20	1.50	ohm

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to $25\text{ }^{\circ}\text{C}$	--	0.6	--	$\text{V}/^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 480\text{ V}, T_C = 125\text{ }^{\circ}\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1050	1365	pF
C_{oss}	Output Capacitance		--	91	119	pF
C_{rss}	Reverse Transfer Capacitance		--	4.5	5.9	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 300\text{ V}, I_D = 7.0\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4,5)	--	17	34	ns
t_r	Turn-On Rise Time		--	12	24	ns
$t_{d(off)}$	Turn-Off Delay Time		--	45	90	ns
t_f	Turn-Off Fall Time		--	15	30	ns
Q_g	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 7.0\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4,5)	--	17	23	nC
Q_{gs}	Gate-Source Charge		--	5	--	nC
Q_{gd}	Gate-Drain Charge		--	5	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I _S	Continuous Source-Drain Diode Forward Current		--	--	5.8	A
I _{SM}	Pulsed Source-Drain Diode Forward Current		--	--	23.2	
V _{SD}	Source-Drain Diode Forward Voltage	I _S = 7.0 A, V _{GS} = 0 V	--	--	1.5	V
t _{rr}	Reverse Recovery Time	I _S = 7.0 A, V _{GS} = 0 V di _F /dt = 100 A/μs (Note 4)	--	340	--	ns
Q _{rr}	Reverse Recovery Charge		--	2.5	--	μC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS}=7.0\text{ A}, V_{DD}=50\text{ V}, R_G=25\text{ }\Omega$, Starting $T_J=25\text{ }^{\circ}\text{C}$
3. $I_{SD}\leq 7.0\text{ A}, di/dt\leq 300\text{ A}/\mu\text{s}, V_{DD}\leq BV_{DSS}$, Starting $T_J=25\text{ }^{\circ}\text{C}$
4. Pulse Test : Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

Typical Characteristics

Figure1. On Region Characteristics

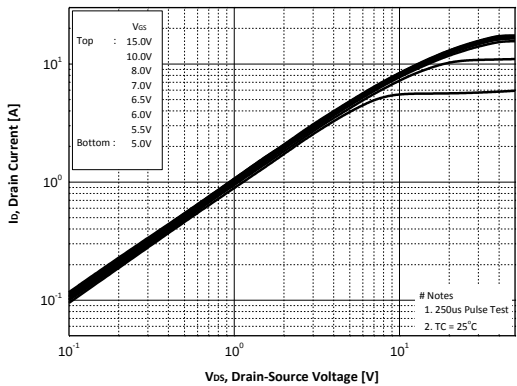


Figure 2. Transfer Characteristics

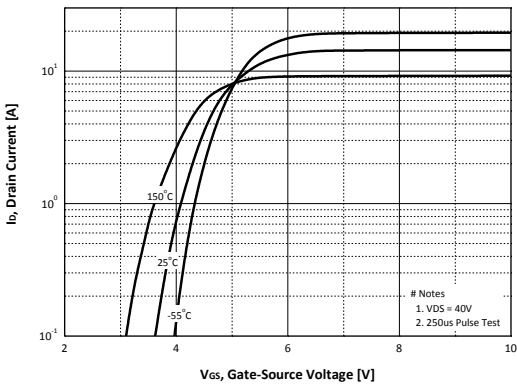


Figure 3. Static Drain-Source On Resistance

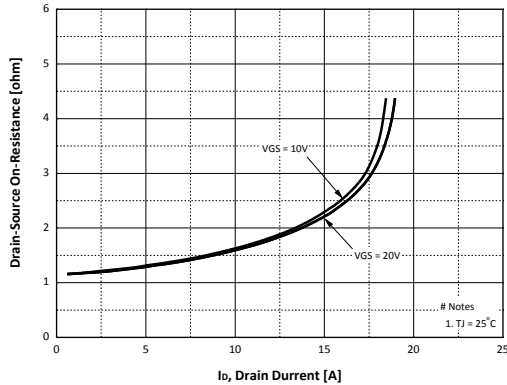


Figure 4. Body Diode Forward Voltage

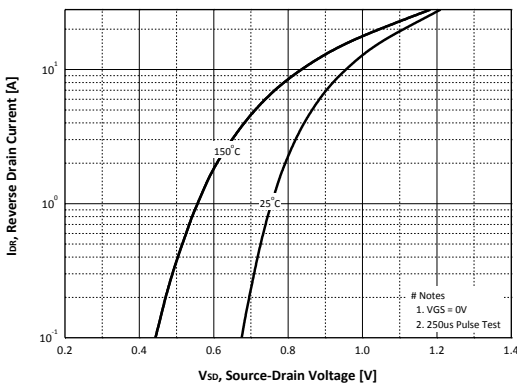


Figure 5. Capacitance Characteristics

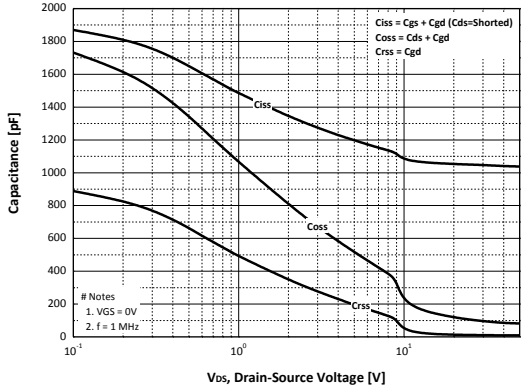
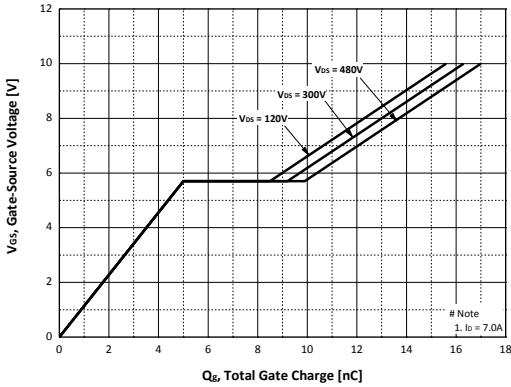


Figure 6. Gate Charge Characteristics



Typical Characteristics (continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

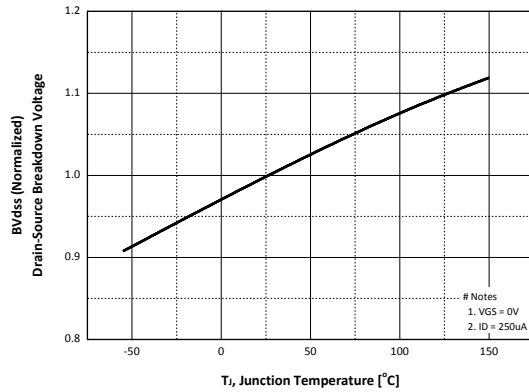


Figure 8. On-Resistance Variation vs. Temperature

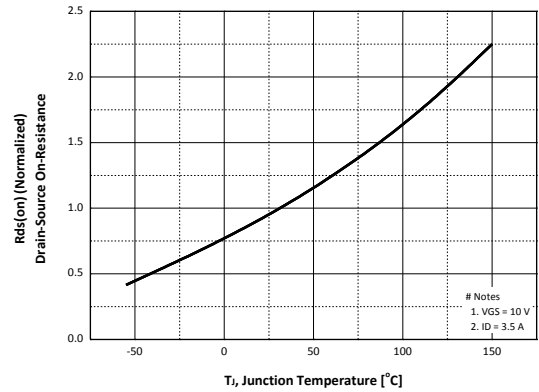


Figure 9. Safe Operation Area

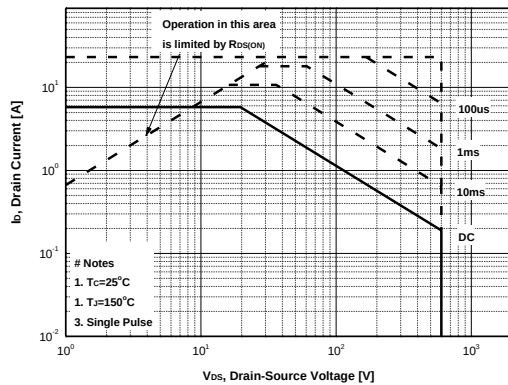


Figure 10. Maximum Drain Current vs. Case Temperature

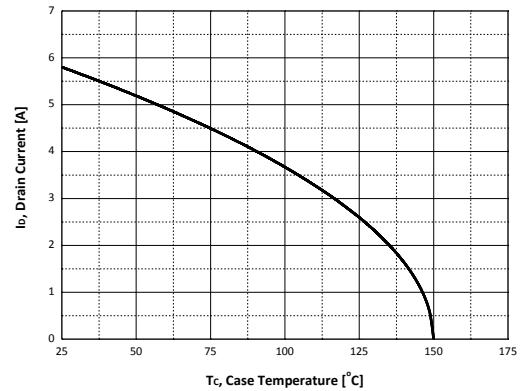
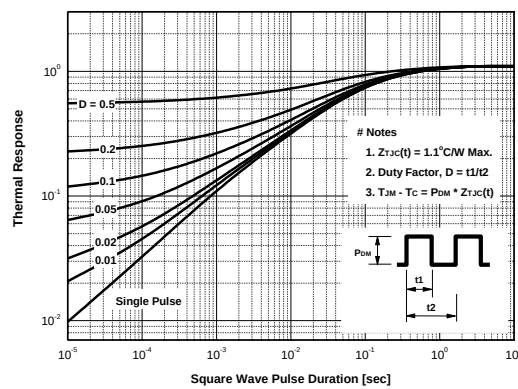


Figure 11. Transient Thermal Response Curve



Characteristics Test Circuit & Waveform

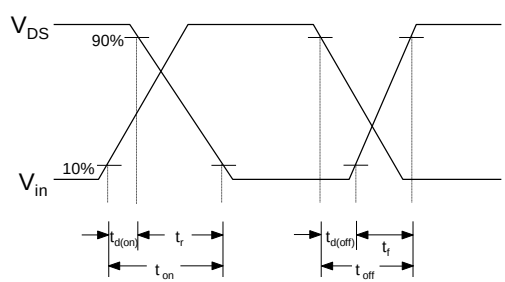
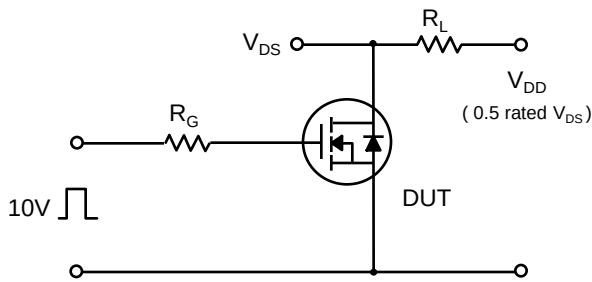


Fig 14. Resistive Switching Test Circuit & Waveforms

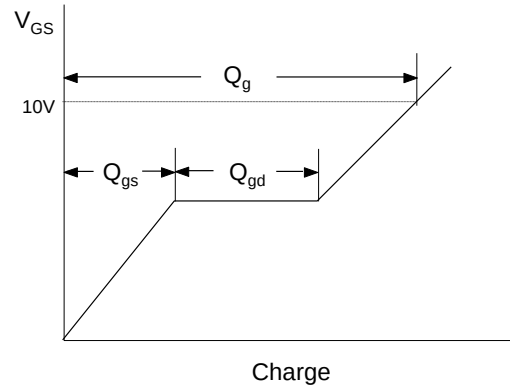
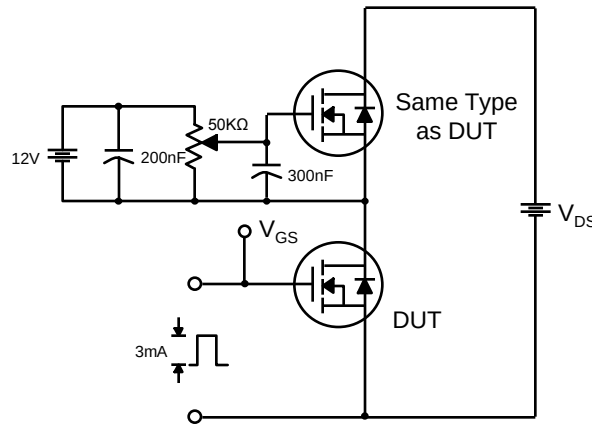


Fig 15. Gate Charge Test Circuit & Waveform

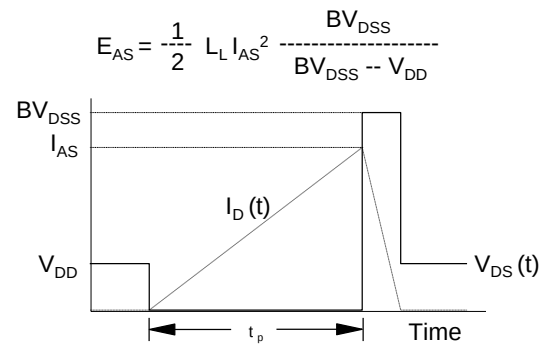
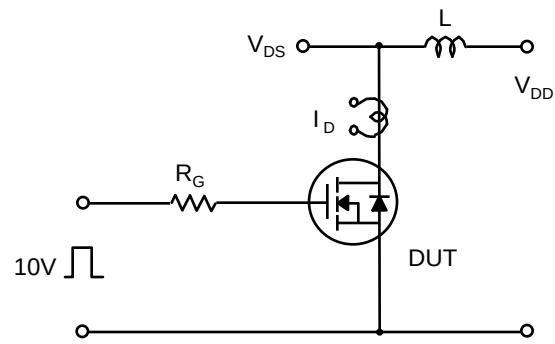


Fig 16. Unclamped Inductive Switching Test Circuit & Waveforms

Characteristics Test Circuit & Waveform (continued)

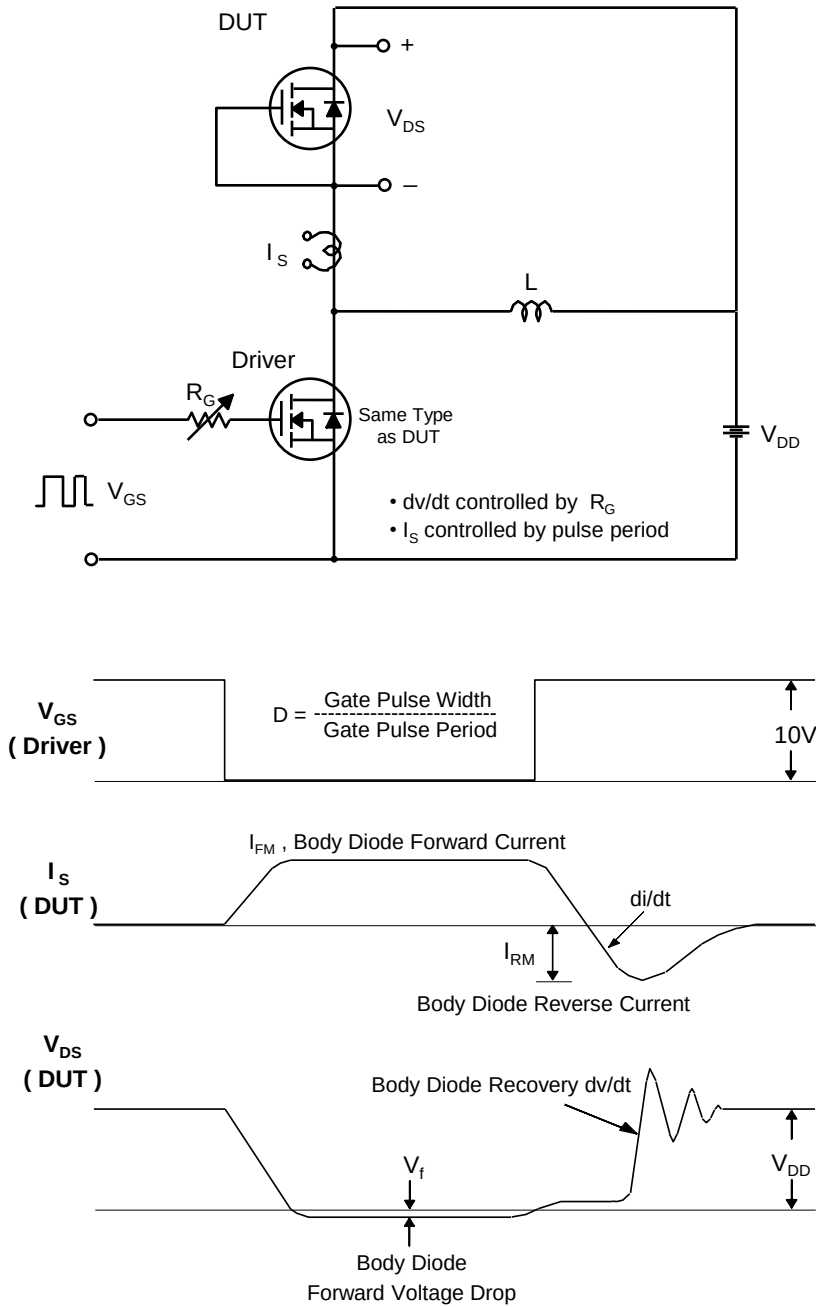
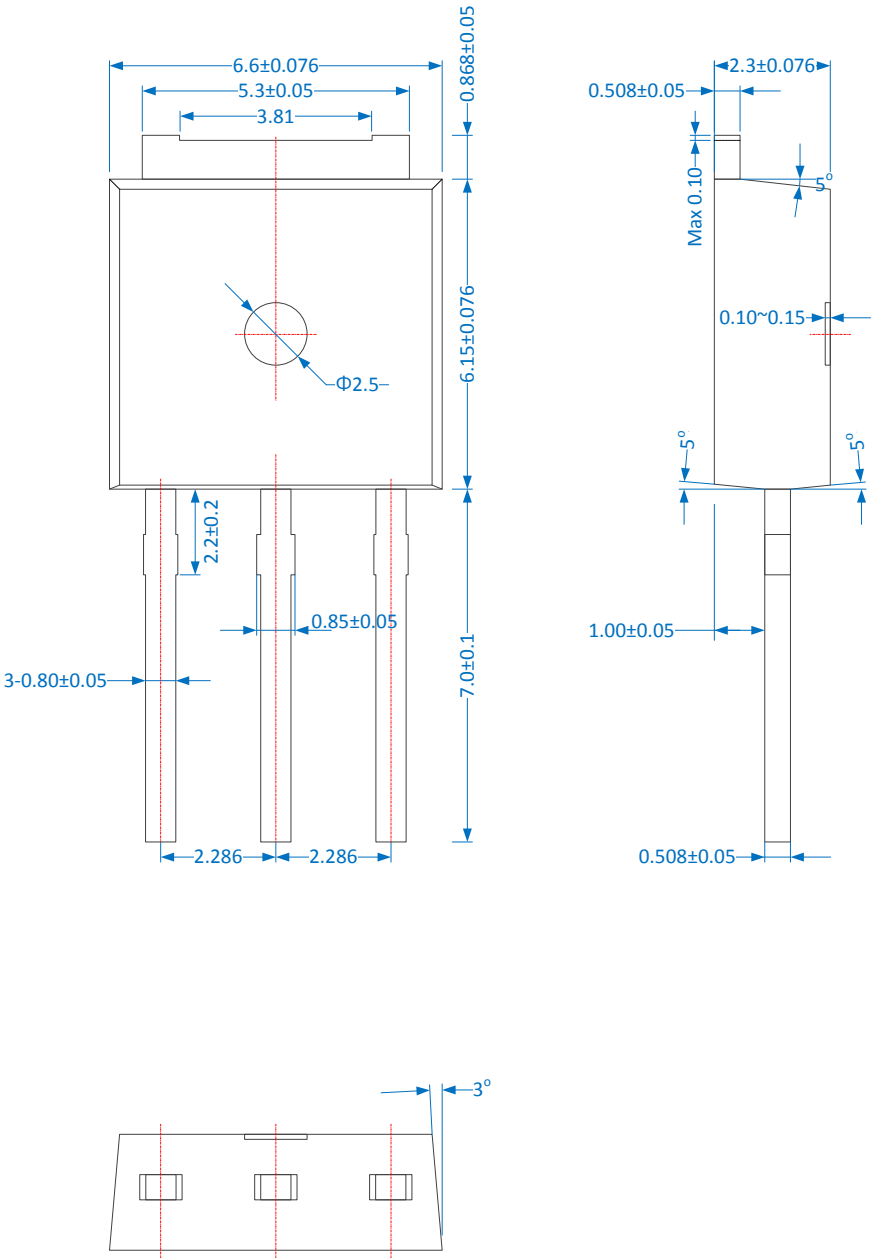


Fig 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Package Dimension

I-PAK(TO-251)



Package Dimension

D-PAK(TO-252)

